

### Abstract of the Disclosure

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A semiconductor device having bonding pad electrode or electrodes of a multi-layer structure. The bonding pad electrode comprises a lower electrode layer formed on a semiconductor substrate, and a cover insulating film formed on the lower electrode layer. The cover insulating film has an opening for exposing at least a portion of the lower electrode layer. A step portion is provided at a side wall of the opening of the cover insulating film. The size of the opening at the upside portion of a step surface of the step portion is larger than the size of the opening at the downside portion of the step surface. The bonding pad electrode further comprises an upper electrode layer formed on the portion of the lower electrode layer exposed via the opening. The upper electrode layer is made of material having corrosion resistance against the substance which is corrosive to the lower electrode layer, and the upper electrode layer overlaps the step surface of the step portion.

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